

General Description

The WSP6047 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP6047 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

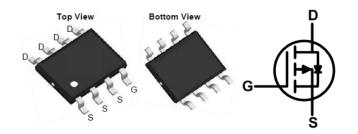
Product Summery

BVDSS	RDSON	ID
-60V	64mΩ	-4.0A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	-60	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25℃	Continuous Drain Current	-4.0	А	
I _D @T _C =70℃	Continuous Drain Current	-2.2	А	
I _{DP}	Pulsed Drain Current	-20	Α	
P _D @T _C =25°C	Total Power Dissipation	2.0	W	
T _J /T _{STG}	Operating/Storage Temperature Range	-55 to 150	°C	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit	
R _{0JA}	Thermal Resistance Junction-Ambient		62	°C/W	
R _{eJC}	Thermal Resistance Junction-Case		4	°C/W	



P-Channel Electrical Characteristics (T_J=25 T, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
В	Static Drain Source On Decistance	V _{GS} =-10V , I _D =-4A		64	84	~ 0
R _{DS(ON)}	Static Drain-Source On-Resistance	V_{GS} =-4.5V , I_D =-3A		80	104	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250uA$	-1.0	-1.74	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-60V , V _{GS} =0V			-1	uA
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, V_{DS} =0V			±100	nA
Qg	Total Gate Charge (-4.5V)	VDS = -30V, ID = -3.5A,		23		
Q _{gs}	Gate-Source Charge	VGS = -10V		2.4		nC
Q_{gd}	Gate-Drain Charge	155 .51		5.7		
$T_{d(on)}$	Turn-On Delay Time			13		
Tr	Rise Time	VDD = -30V, ID = -1A,		4		ns
$T_{d(off)}$	Turn-Off Delay Time	VGS = -10V, RGEN = 6Ω		45		. 115
T _f	Fall Time			6		
C _{iss}	Input Capacitance			1135		
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} = -30V, f=1MHz		95		pF
C _{rss}	Reverse Transfer Capacitance			60		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V _G =V _D =0V , Force Current			-4.0	Α
V_{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V

A: The value of R $_{\theta \text{ JA}}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with TA=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



P-Ch MOSFET

P-Channel Typical Characteristics

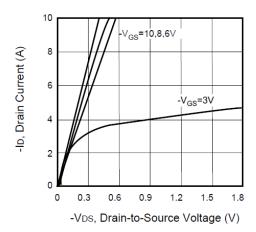


Figure 1. Output Characteristics

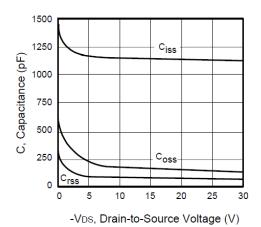


Figure 3. Capacitance

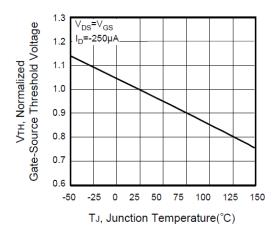


Figure 5. Gate Threshold Variation with Temperature

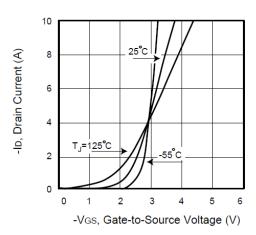


Figure 2. Transfer Characteristics

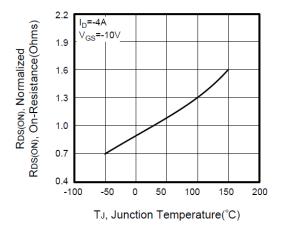


Figure 4. On-Resistance Variation with Temperature

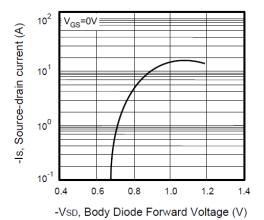


Figure 6. Body Diode Forward Voltage Variation with Source Current



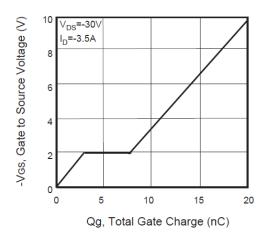


Figure 7. Gate Charge

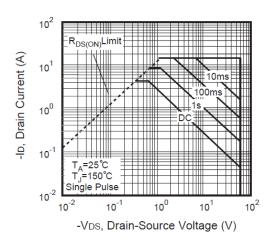


Figure 8. Maximum Safe Operating Area

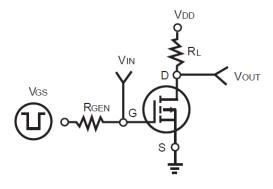


Figure 9. Switching Test Circuit

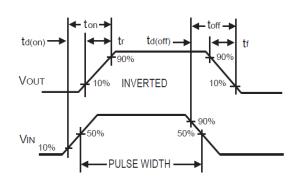


Figure 10. Switching Waveforms

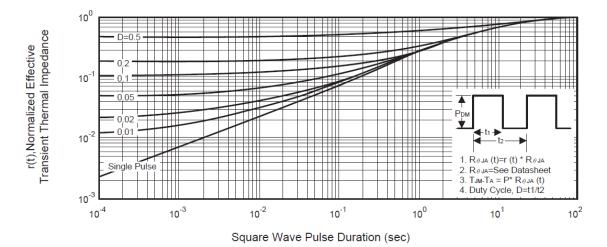


Figure 11. Normalized Thermal Transient Impedance Curve



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